

Power management (dual transistors)

UMF6N

2SA2018 and 2SK3019 are housed independently in a UMT package.

●Application

Power management circuit

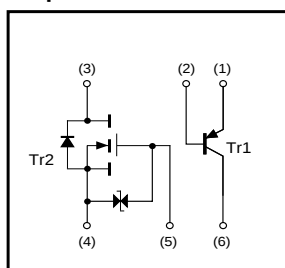
●Features

- 1) Power switching circuit in a single package.
- 2) Mounting cost and area can be cut in half.

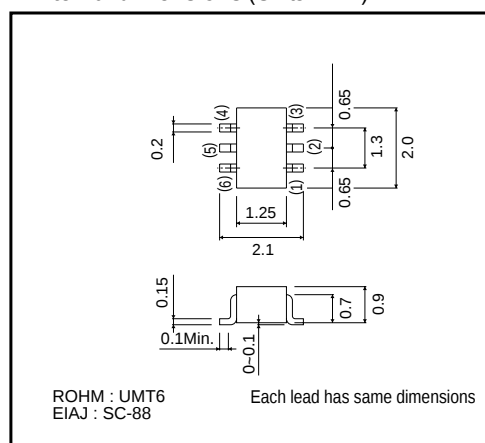
●Structure

Silicon epitaxial planar transistor

●Equivalent circuits



●External dimensions (Units : mm)



●Packaging specifications

Type	UMF6N
Package	UMT6
Marking	F6
Code	TR
Basic ordering unit (pieces)	3000

Transistors

●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CBO}	−15	V
Collector-emitter voltage	V _{CEO}	−12	V
Emitter-base voltage	V _{EBO}	−6	V
Collector current	I _C	−500	mA
	I _{CP}	−1.0	A *1
Power dissipation	P _C	150(TOTAL)	mW *2
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55~+150	°C

*1 Single pulse P_W=1ms

*2 120mW per element must not be exceeded. Each terminal mounted on a recommended land.

Tr2

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	±20	V
Drain current	Continuous I _D	100	mA
	Pulsed I _{DP}	200	mA *1
Reverse drain current	Continuous I _{DR}	100	mA
	Pulsed I _{DRP}	200	mA *1
Total power dissipation	P _D	150(TOTAL)	mW *2
Channel temperature	T _{ch}	150	°C
Range of storage temperature	T _{stg}	−55~+150	°C

*1 P_W≤10ms Duty cycles≤50%

*2 120mW per element must not be exceeded. Each terminal mounted on a recommended land.

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV _{CEO}	−12	−	−	V	I _C =−1mA
Collector-base breakdown voltage	BV _{CBO}	−15	−	−	V	I _C =−10μA
Emitter-base breakdown voltage	BV _{EBO}	−6	−	−	V	I _E =−10μA
Collector cut-off current	I _{CBO}	−	−	−100	nA	V _{CB} =−15V
Emitter cut-off current	I _{EBO}	−	−	−100	nA	V _{EB} =−6V
Collector-emitter saturation voltage	V _{CE(sat)}	−	−100	−250	mV	I _C =−200mA, I _B =−10mA
DC current gain	h _{FE}	270	−	680	−	V _{CE} =−2V, I _C =−10mA
Transition frequency	f _T	−	260	−	MHz	V _{CE} =−2V, I _E =10mA, f=100MHz
Collector output capacitance	C _{ob}	−	6.5	−	pF	V _{CB} =−10V, I _E =0mA, f=1MHz

Tr2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	−	−	±1	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	30	−	−	V	I _D =10μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	−	−	1.0	μA	V _{DS} =30V, V _{GS} =0V
Gate-threshold voltage	V _{GS(th)}	0.8	−	1.5	V	V _{DS} =3V, I _D =100μA
Static drain-source on-state resistance	R _{DS(on)}	−	5	8	Ω	I _D =10mA, V _{GS} =4V
		−	7	13	Ω	I _D =1mA, V _{GS} =2.5V
Forward transfer admittance	Y _{fs}	20	−	−	ms	V _{DS} =3V, I _D =10mA
Input capacitance	C _{iss}	−	13	−	pF	V _{DS} =5V, V _{GS} =0V, f=1MHz
Output capacitance	C _{oss}	−	9	−	pF	
Reverse transfer capacitance	C _{rss}	−	4	−	pF	
Turn-on delay time	t _{d(on)}	−	15	−	ns	I _D =10mA, V _{DD} =5V, V _{GS} =5V, R _L =500Ω, R _{GS} =10Ω
Rise time	t _r	−	35	−	ns	
Turn-off delay time	t _{d(off)}	−	80	−	ns	
Fall time	t _f	−	80	−	ns	

Transistors

●Electrical characteristic curves

Tr1

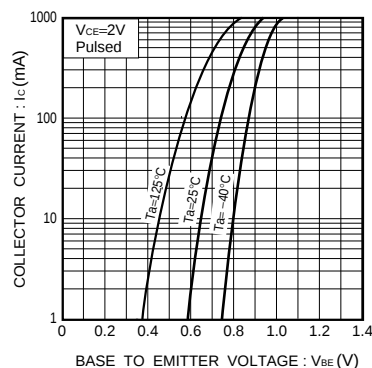


Fig.1 Grounded emitter propagation characteristics

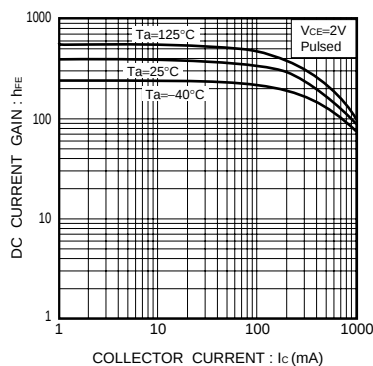


Fig.2 DC current gain vs. collector current

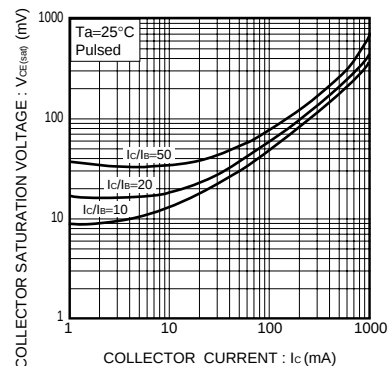
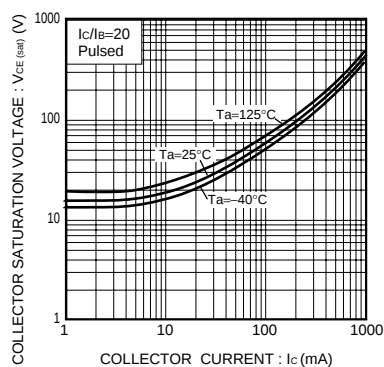
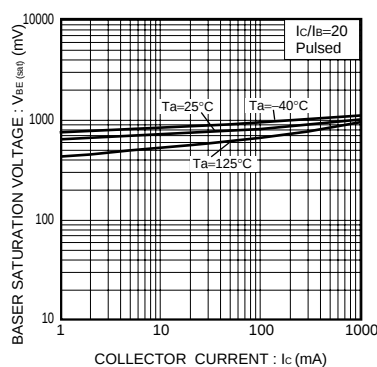
Fig.3 Collector-emitter saturation voltage vs. collector current (I)Fig.4 Collector-emitter saturation voltage vs. collector current (II)

Fig.5 Base-emitter saturation voltage vs. collector current

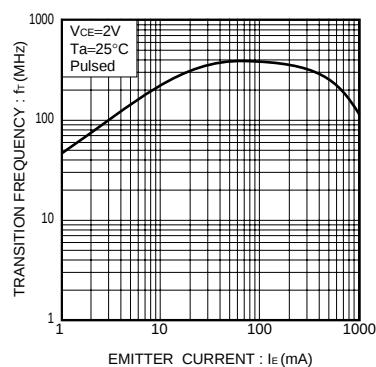


Fig.6 Gain bandwidth product vs. emitter current

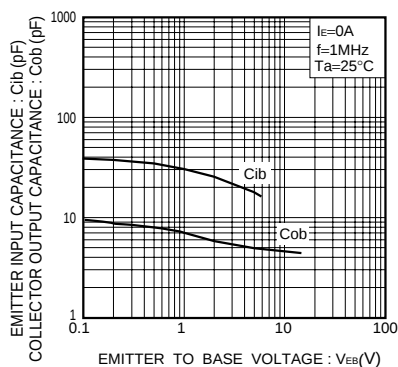
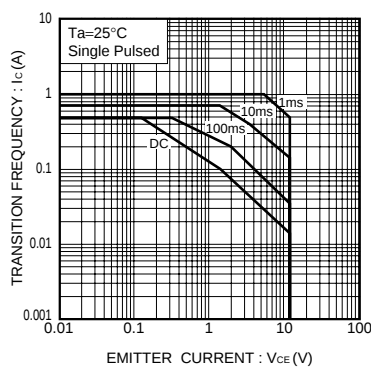
Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Fig.8 Safe operation area

Transistors

Tr2

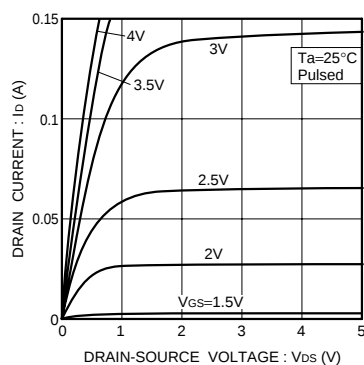


Fig.9 Typical output characteristics

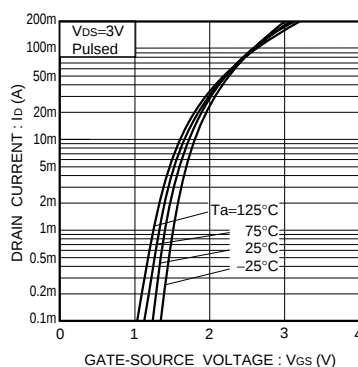


Fig.10 Typical transfer characteristics

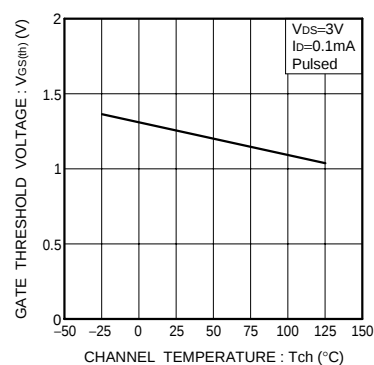


Fig.11 Gate threshold voltage vs. channel temperature

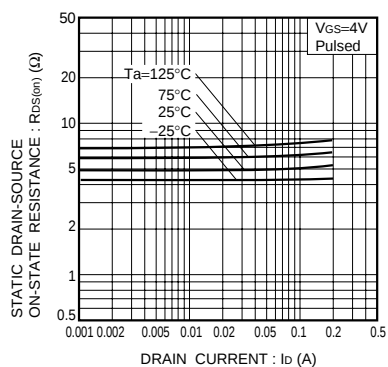


Fig.12 Static drain-source on-state resistance vs. drain current (I)

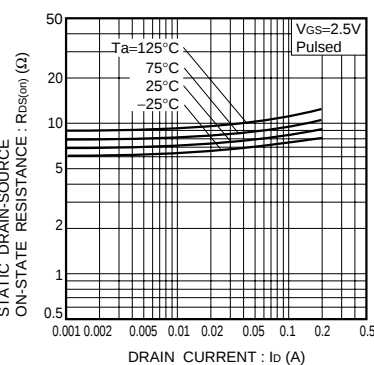


Fig.13 Static drain-source on-state resistance vs. drain current (II)

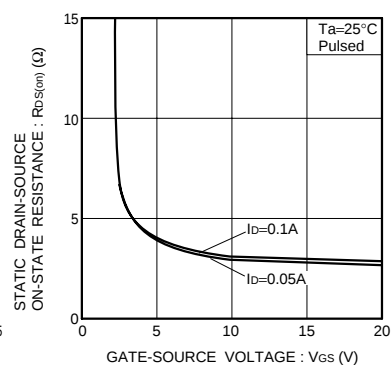


Fig.14 Static drain-source on-state resistance vs. gate-source voltage

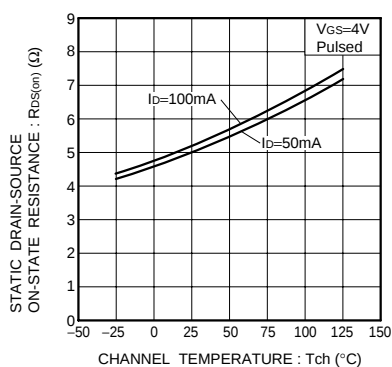


Fig.15 Static drain-source on-state resistance vs. channel temperature

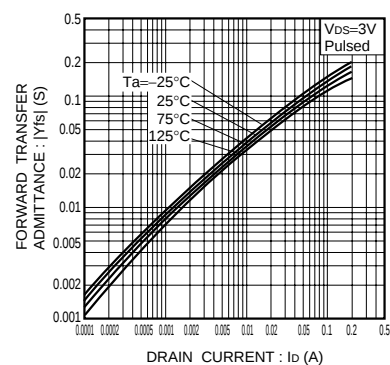


Fig.16 Forward transfer admittance vs. drain current

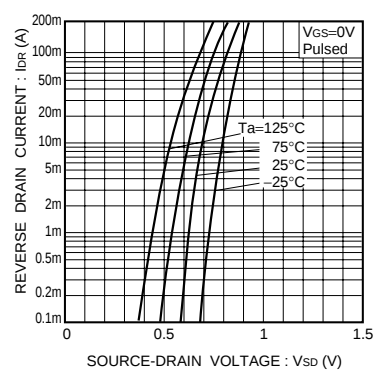


Fig.17 Reverse drain current vs. source-drain voltage (I)

Transistors

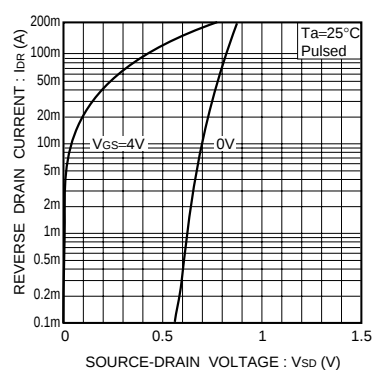


Fig.18 Reverse drain current vs. source-drain voltage (II)

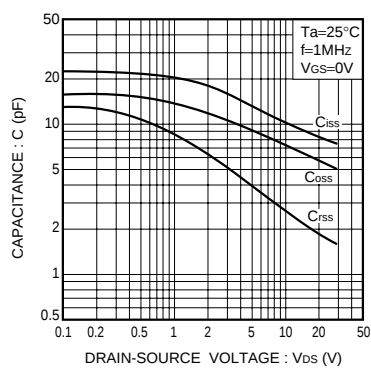


Fig.19 Typical capacitance vs. drain-source voltage

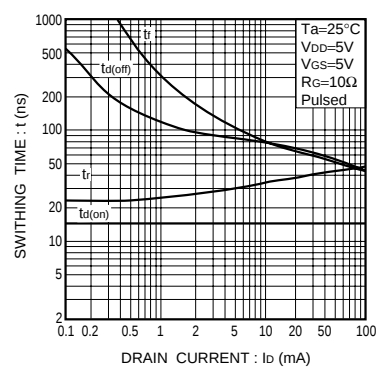


Fig.20 Switching characteristics

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